

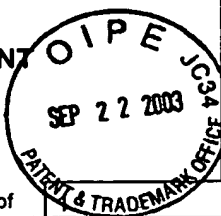
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**INFORMATION DISCLOSURE STATEMENT
BY APPLICANT**



Applicant: Florin UDREA

Appln. No.: 10/602,065

Filing Date: June 24, 2003

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Page

1

of

Examiner: UNKNOWN

Group Art Unit: 2812 2814

U.S. PATENT DOCUMENTS

Examiner's Initials*		Document Number	Date MM/YYYY	Name (Family Name of First Inventor)	Class	Sub Class	Filing Date (if appropriate)
HP	AR	2002/0041003	04/2002	UDREA et al.			
	BR						
	CR						
	DR						
	ER						
	FR						
	GR						
	HR						
	IR						
	JR						
	KR						
	LR						
	MR						
	NR						

FOREIGN PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS							English Abstract		Translation Readily Available	
		Document Number	Date MM/YYYY	Country	Inventor Name		Enclosed	No	Enclose	No
HP	OR	WO 02/25700A2	03/2002	PCT	UDREA et al.					
	PR									
	QR									
	RR									
	SR									
	TR									
	UR									
	VR									

OTHER (Including in this order Author, Title, Periodical Name, Date, Pertinent Pages, etc.)

HP	WR	Udrea et al., "3D RESURF double-gate MOSFET: A revolutionary power device concept," <i>Electronics Letters</i> 34(8):808-809 (1998)							
	XR								
	YR								
	ZR								
	AAR								
	BBR								
	CCR								

Examiner

Udrea et al.

Date Considered:

9/22/04

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.